

SANYO	No.1685A	<h1 style="margin: 0;">2SA1423/2SC3656</h1> <p style="margin: 0;">PNP/NPN Epitaxial Planar Silicon Transistors</p> <h2 style="margin: 0;">Switching Applications</h2> <p style="margin: 0;">(with Bias Resistor)</p>
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Use

. Switching circuit, inverter circuit, interface circuit, driver circuit.

Features

. With bias resistor ($R1=10k\Omega$, $R2=10k\Omega$).

(): 2SA1423

Absolute Maximum Ratings at $T_a=25^\circ C$

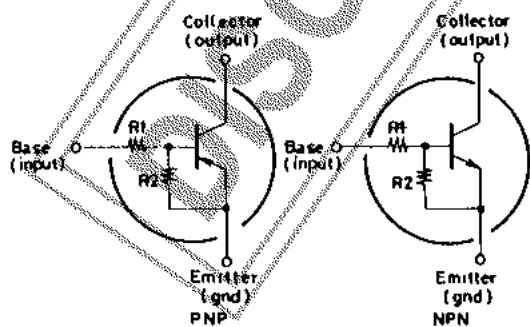
			unit
Collector to Base Voltage	V_{CBO}	(-)50	V
Collector to Emitter Voltage	V_{CEO}	(-)50	V
Emitter to Base Voltage	V_{EBO}	(-)10	V
Collector Current	I_C	(-)100	mA
Collector Current(Pulse)	I_{CP}	(-)200	mA
Collector Dissipation	P_C	400	mW
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature	T_{stg}	-55 to +150	$^\circ C$

Electrical Characteristics at $T_a=25^\circ C$

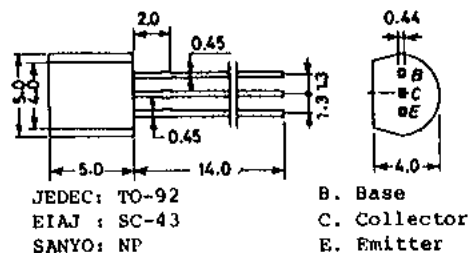
		min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB}=(-)40V, I_E=0$		(-)0.1	μA
Collector Cutoff Current	I_{CEO}	$V_{CE}=(-)40V, I_B=0$		(-)0.5	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=(-)5V, I_C=0$		(-)170(-)250(-)330	μA
DC Current Gain	h_{FE}	$V_{CE}=(-)5V, I_C=(-)10mA$	50		
Gain-Bandwidth Product	f_T	$V_{CE}=(-)10V, I_C=(-)5mA$		250	MHz
			(200)		
Output Capacitance	c_{ob}	$V_{CB}=(-)10V, f=1MHz$		3.7	pF
				(5.5)	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=(-)10mA, I_B=(-)0.5mA$		(-)0.1(-)0.3	V
Collector to Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=(-)10\mu A, I_E=0$		(-)50	V
Collector to Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=(-)100\mu A, R_{BE}=\infty$		(-)50	V

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Electrical Connection



Case Outline 2003A
(unit:mm)



Specifications and information herein are subject to change without notice.

SANYO Electric Co., Ltd. Semiconductor Business Headquarters
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110 JAPAN

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			min	typ	max	unit
Input OFF-State Voltage	$V_{I(off)}$	$V_{CE}=(-)5V, I_C=(-)100\mu A$	(-)0.8	(-)1.1	(-)1.5	V
Input ON-State Voltage	$V_{I(on)}$	$V_{CE}=(-)0.2V, I_C=(-)10mA$	(-)1.0	(-)2.0	(-)4.0	V
Input Resistance	R_1		7.0	10	13	k Ω
Resistance Ratio	R_1/R_2		0.9	1.0	1.1	-

Sample Application Circuit

